# **74AUP2G14**

# Low-power dual Schmitt trigger inverter Rev. 6 — 17 September 2015

**Product data sheet** 

#### **General description** 1.

The 74AUP2G14 provides two inverting buffers with Schmitt trigger action which accept standard input signals. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

This device ensures a very low static and dynamic power consumption across the entire V<sub>CC</sub> range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage  $V_{T+}$  and the negative voltage  $V_{T-}$  is defined as the input hysteresis voltage V<sub>H</sub>.

#### Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

# **Applications**

- Wave and pulse shaper
- Astable multivibrator
- Monostable multivibrator



**74AUP2G14** 

# 4. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AUP2G14GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363					
74AUP2G14GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886					
74AUP2G14GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891					
74AUP2G14GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115					
74AUP2G14GS	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 $\times$ 1.0 $\times$ 0.35 mm	SOT1202					
74AUP2G14GX	–40 °C to +125 °C	X2SON6	plastic thermal extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 0.8 $\times$ 0.35 mm	SOT1255					

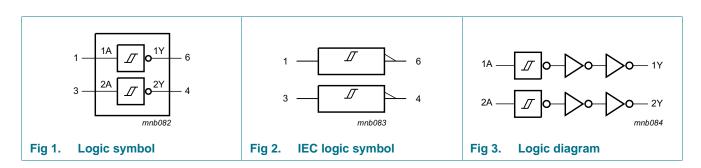
# 5. Marking

#### Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74AUP2G14GW	рК
74AUP2G14GM	рК
74AUP2G14GF	рК
74AUP2G14GN	рК
74AUP2G14GS	рК
74AUP2G14GX	рК

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

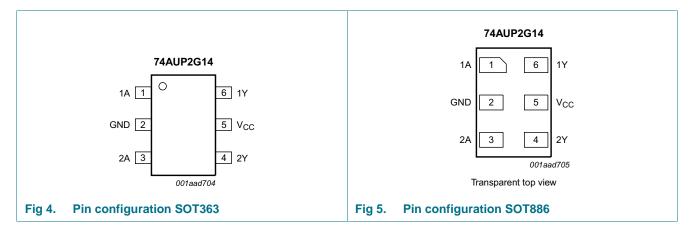
# 6. Functional diagram



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# 7. Pinning information

#### 7.1 Pinning





# 7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V <sub>CC</sub>	5	supply voltage
1Y	6	data output

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# 8. Functional description

Table 4. Function table[1]

Input	Output
nA	nY
L	Н
Н	L

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level.

# 9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V		-50	-	mA
VI	input voltage		[1]	-0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V		-50	-	mA
Vo	output voltage	Active mode and Power-down mode	[1]	-0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$		-	±20	mA
I <sub>CC</sub>	supply current			-	50	mA
I <sub>GND</sub>	ground current			-50	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[2]	-	250	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

# 10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V <sub>CC</sub>	V
		Power-down mode; V <sub>CC</sub> = 0 V	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C

<sup>[2]</sup> For SC-88 packages: above 87.5  $^{\circ}$ C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K. For X2SON6 and XSON6 packages: above 118  $^{\circ}$ C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

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# 11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					-
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = -20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V <sub>CC</sub> - 0.1	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = 20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.31	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.44	V
l <sub>l</sub>	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I <sub>CC</sub>	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
Δl <sub>CC</sub>	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	40	μА
Cı	input capacitance	$V_I = GND \text{ or } V_{CC}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	1.1	-	pF
Co	output capacitance	$V_O = GND$ ; $V_{CC} = 0 V$	-	1.7	-	pF
T <sub>amb</sub> = -	40 °C to +85 °C					
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = -20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V <sub>CC</sub> - 0.1	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.7 × V <sub>CC</sub>	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
		, 00				

## Low-power dual Schmitt trigger inverter

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I <sub>I</sub>	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O} = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$	-	-	±0.5	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1 \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μА
I <sub>CC</sub>	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μΑ
Δl <sub>CC</sub>	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ
T <sub>amb</sub> = -	40 °C to +125 °C					
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O} = -20 \mu A$ ; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V <sub>CC</sub> - 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = 20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.41	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.39	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l <sub>l</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.75	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_1$ or $V_0 = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$	-	-	±0.75	μΑ

## Low-power dual Schmitt trigger inverter

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\Delta I_{OFF}$	additional power-off leakage current	$V_{I}$ or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I <sub>CC</sub>	supply current	$V_I$ = GND or $V_{CC}$ ; $I_O$ = 0 A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	1.4	μΑ
Δl <sub>CC</sub>	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

# 12. Dynamic characteristics

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		-4	10 °C to +′	125 °C	Unit
				Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 p$	F				•				
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 8							
		V <sub>CC</sub> = 0.8 V	-	19.9	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.7	5.9	11.0	2.4	11.1	11.2	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.6	4.3	6.6	2.4	7.1	7.4	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.1	3.7	5.4	2.0	6.0	6.2	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.0	3.0	4.1	1.7	4.5	4.7	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.9	2.8	3.6	1.5	3.9	4.0	ns
C <sub>L</sub> = 10	pF							1	
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 8 [2]							
		V <sub>CC</sub> = 0.8 V	-	23.4	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.9	6.8	12.7	2.8	12.8	12.9	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.8	5.0	7.7	2.6	8.2	8.6	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.7	4.2	6.2	2.5	6.7	7.1	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.3	3.6	4.8	2.1	5.2	5.5	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.1	3.3	4.3	2.0	4.5	4.7	ns
C <sub>L</sub> = 15	pF	1		1			1	1	
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 8							
		V <sub>CC</sub> = 0.8 V	-	26.9	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	3.3	7.6	14.3	3.0	14.5	14.7	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.3	5.5	8.6	2.9	9.4	9.8	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.8	4.7	7.0	2.8	7.7	8.1	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.7	4.0	5.5	2.4	5.9	6.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.6	3.8	4.8	2.2	5.2	5.4	ns

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 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		_4	l0 °C to +1	125 °C	Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 30	pF								
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 8 [2]							
		V <sub>CC</sub> = 0.8 V	-	37.3	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	4.0	9.8	18.7	3.9	19.6	20.0	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	3.7	7.1	11.2	3.8	12.3	12.9	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	3.6	6.0	9.1	3.6	10.0	10.6	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	3.5	5.2	6.9	3.2	7.5	7.9	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	3.3	4.8	6.1	3.1	7.1	7.4	ns
$C_L = 5 p$	F, 10 pF, 15 pF and	30 pF			1				1
C <sub>PD</sub>	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ [3][4]							
	capacitance	V <sub>CC</sub> = 0.8 V	-	2.6	-	-	-	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	2.7	-	-	-	-	pF
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	2.9	-	-	-	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	3.1	-	-	-	-	pF
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	3.7	-	-	-	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	4.3	-	-	-	-	pF

- [1] All typical values are measured at nominal V<sub>CC</sub>.
- [2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [3] All specified values are the average typical values over all stated loads.
- [4]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

 $f_i$  = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = load capacitance in pF;

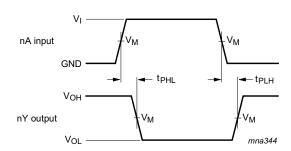
 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$  = sum of the outputs.

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#### 13. Waveforms



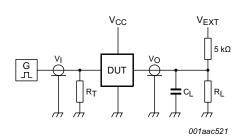
Measurement points are given in Table 9.

Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

Fig 8. The data input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input					
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	VI	$t_r = t_f$			
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V <sub>CC</sub>	≤ 3.0 ns			



Test data is given in Table 10.

Definitions for test circuit:

 $R_L$  = Load resistance.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

 $V_{EXT}$  = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V <sub>EXT</sub>			
V <sub>CC</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>	
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2 \times V_{CC}$	

[1] For measuring enable and disable times  $R_L$  = 5 k $\Omega$ , for measuring propagation delays, set-up and hold times and pulse width  $R_L$  = 1 M $\Omega$ .

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Low-power dual Schmitt trigger inverter

# 14. Transfer characteristics

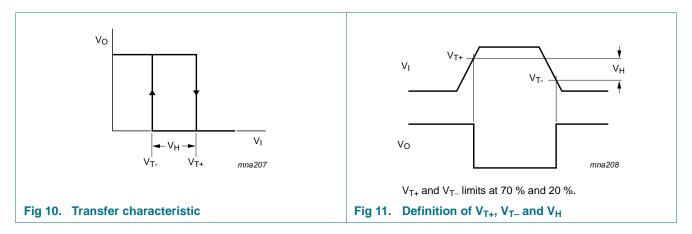
Table 11. Transfer characteristics

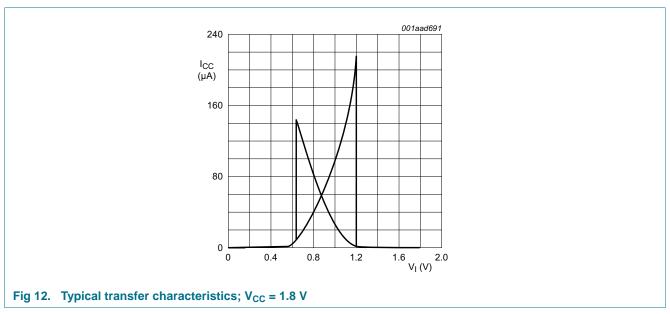
Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		-40	°C to +12	25 °C	Unit
			Min	Тур	Max	Min	Max (85 °C)	Max (125 °C)	
V <sub>T+</sub>	positive-going threshold voltage	see Figure 10 and Figure 11							
		V <sub>CC</sub> = 0.8 V	0.30	-	0.60	0.30	0.60	0.62	V
		V <sub>CC</sub> = 1.1 V	0.53	-	0.90	0.53	0.90	0.92	V
		V <sub>CC</sub> = 1.4 V	0.74	-	1.11	0.74	1.11	1.13	V
		V <sub>CC</sub> = 1.65 V	0.91	-	1.29	0.91	1.29	1.31	V
		V <sub>CC</sub> = 2.3 V	1.37	-	1.77	1.37	1.77	1.80	V
		V <sub>CC</sub> = 3.0 V	1.88	-	2.29	1.88	2.29	2.32	V
$V_{T-}$	V <sub>T-</sub> negative-going threshold voltage	see Figure 10 and Figure 11							
		V <sub>CC</sub> = 0.8 V	0.10	-	0.60	0.10	0.60	0.60	V
		V <sub>CC</sub> = 1.1 V	0.26	-	0.65	0.26	0.65	0.65	V
		V <sub>CC</sub> = 1.4 V	0.39	-	0.75	0.39	0.75	0.75	V
		V <sub>CC</sub> = 1.65 V	0.47	-	0.84	0.47	0.84	0.84	V
	V <sub>CC</sub> = 2.3 V	0.69	-	1.04	0.69	1.04	1.04	V	
		V <sub>CC</sub> = 3.0 V	0.88	-	1.24	0.88	1.24	1.24	V
V <sub>H</sub>	hysteresis voltage	(V <sub>T+</sub> – V <sub>T-</sub> ); see <u>Figure 10</u> , <u>Figure 11</u> , <u>Figure 12</u> and <u>Figure 13</u>							
		V <sub>CC</sub> = 0.8 V	0.07	-	0.50	0.07	0.50	0.50	V
		V <sub>CC</sub> = 1.1 V	0.08	-	0.46	0.08	0.46	0.46	V
		V <sub>CC</sub> = 1.4 V	0.18	-	0.56	0.18	0.56	0.56	V
		V <sub>CC</sub> = 1.65 V	0.27	-	0.66	0.27	0.66	0.66	V
		V <sub>CC</sub> = 2.3 V	0.53	-	0.92	0.53	0.92	0.92	V
		V <sub>CC</sub> = 3.0 V	0.79	-	1.31	0.79	1.31	1.31	V

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# 15. Waveforms transfer characteristics





#### Low-power dual Schmitt trigger inverter

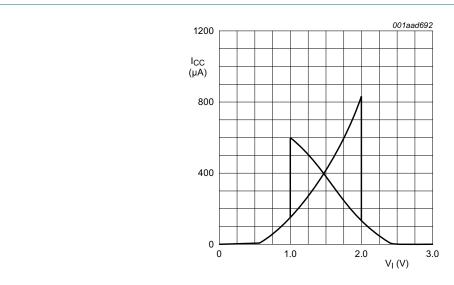


Fig 13. Typical transfer characteristics;  $V_{CC} = 3.0 \text{ V}$ 

# 16. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

 $P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC}$  where:

 $P_{add}$  = additional power dissipation ( $\mu W$ );

 $f_i = input frequency (MHz);$ 

 $t_r$  = rise time (ns); 10 % to 90 %;

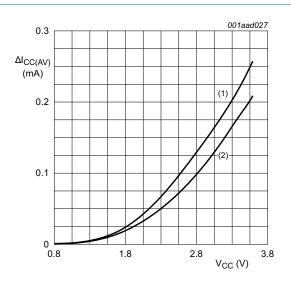
 $t_f = fall time (ns); 90 \% to 10 \%;$ 

 $\Delta I_{CC(AV)}$  = average additional supply current ( $\mu A$ ).

Average  $\Delta I_{CC(AV)}$  differs with positive or negative input transitions, as shown in Figure 14.

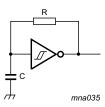
An example of a relaxation circuit using the 74AUP2G14 is shown in Figure 15.

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- (1) Positive-going edge.
- (2) Negative-going edge.

Fig 14. Average  $I_{CC}$  as a function of  $V_{CC}$ 



$$f = \frac{I}{T} \approx \frac{I}{a \times RC}$$

Average values for variable a are given in Table 12.

Fig 15. Relaxation oscillator

Table 12. Variable values

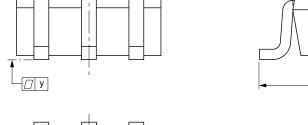
Supply voltage	Variable a
1.1 V	1.28
1.5 V	1.22
1.8 V	1.24
2.8 V	1.34
3.3 V	1.45

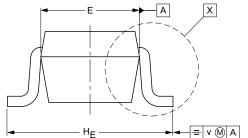
**SOT363** 

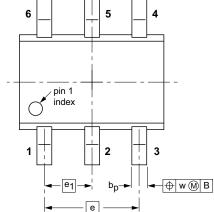
# 17. Package outline

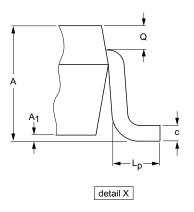
Plastic surface-mounted package; 6 leads

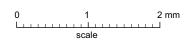
# D B E











#### **DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub> max	bp	С	D	Е	е	e <sub>1</sub>	HE	Lp	Ø	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFERENCES				ICCUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT363			SC-88			<del>04-11-08</del> 06-03-16	

Fig 16. Package outline SOT363 (SC-88)

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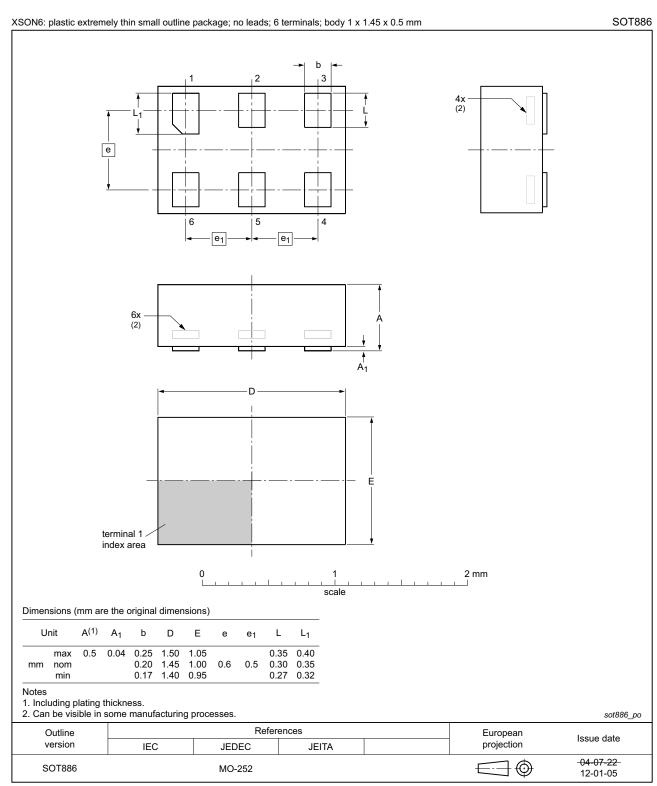


Fig 17. Package outline SOT886 (XSON6)

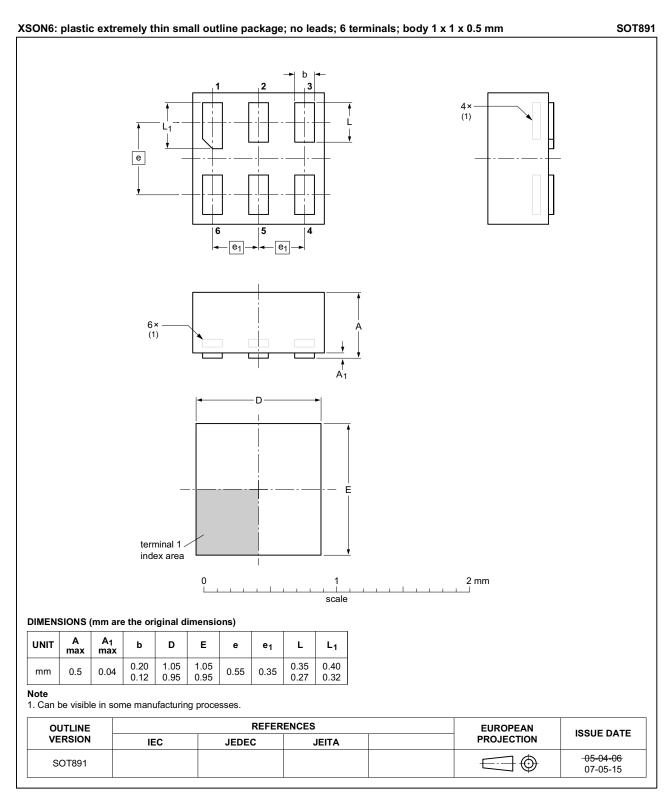


Fig 18. Package outline SOT891 (XSON6)

**Product data sheet** 

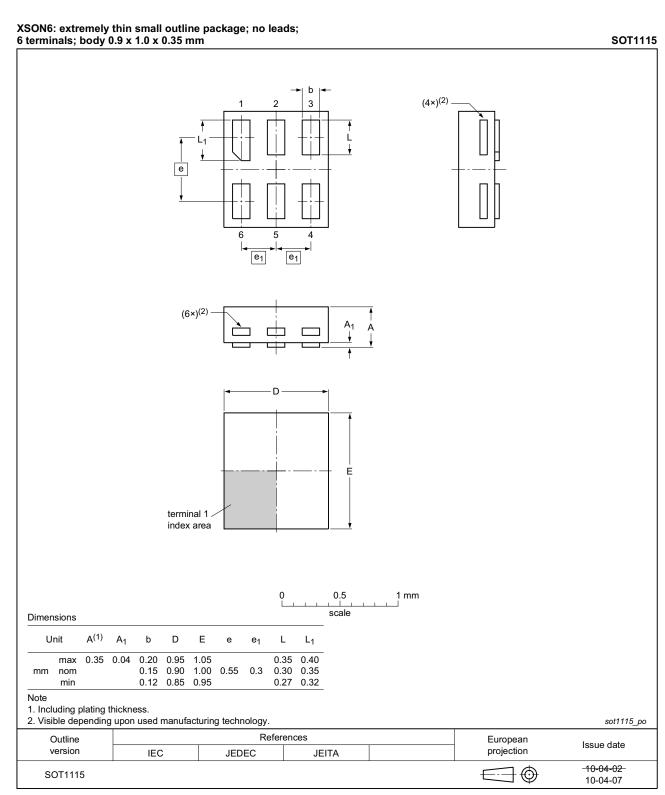


Fig 19. Package outline SOT1115 (XSON6)

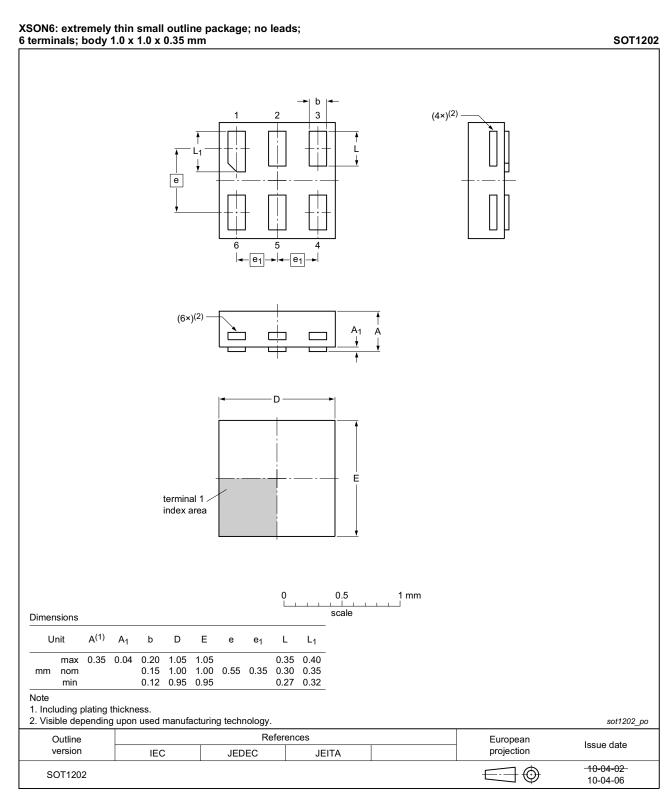


Fig 20. Package outline SOT1202 (XSON6)

**Product data sheet** 

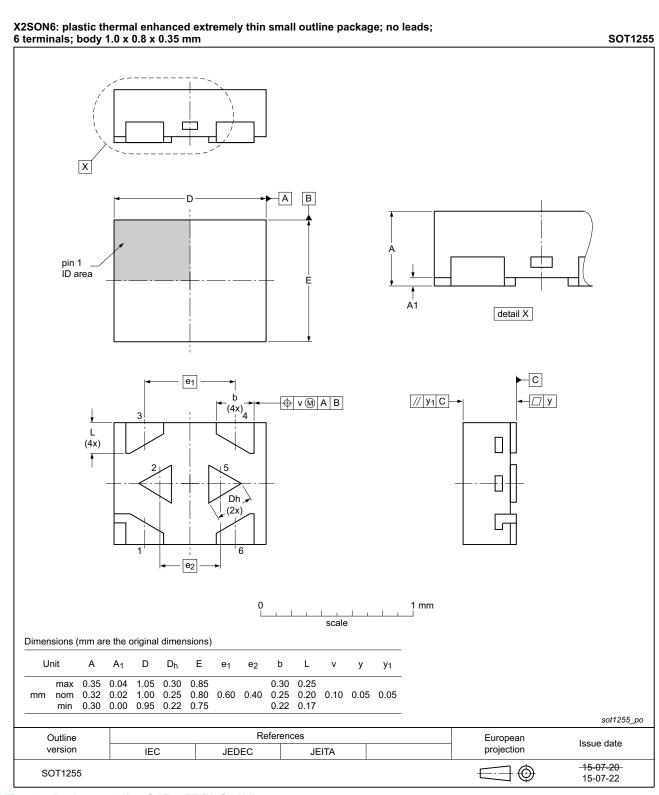


Fig 21. Package outline SOT1255 (X2SON6)

## Low-power dual Schmitt trigger inverter

# 18. Abbreviations

#### Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

# 19. Revision history

#### Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G14 v.6	20150917	Product data sheet	-	74AUP2G14 v.5
Modifications:	Added type	number 74AUP2G14GX (S	SOT1255/X2SON6).	
74AUP2G14 v.5	20121204	Product data sheet	-	74AUP2G14 v.4
Modifications:	Package o	utline drawing of SOT886 (F	igure 17) modified.	
74AUP2G14 v.4	20111201	Product data sheet	-	74AUP2G14 v.3
74AUP2G14 v.3	20100722	Product data sheet	-	74AUP2G14 v.2
74AUP2G14 v.2	20090703	Product data sheet	-	74AUP2G14 v.1
74AUP2G14 v.1	20061219	Product data sheet	-	-

#### Low-power dual Schmitt trigger inverter

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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#### Low-power dual Schmitt trigger inverter

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